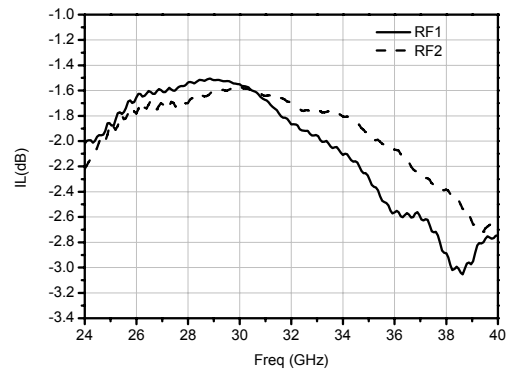
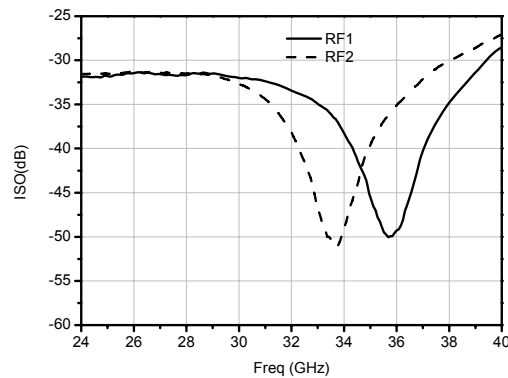


Insertion Loss

Isolation

Features

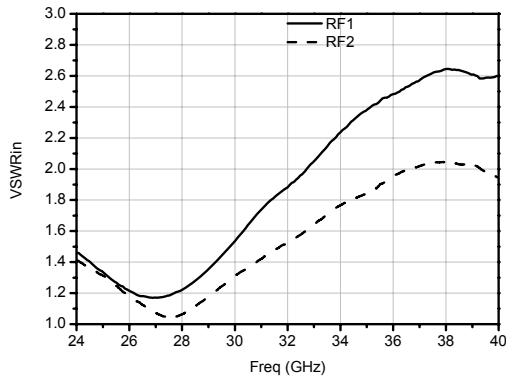
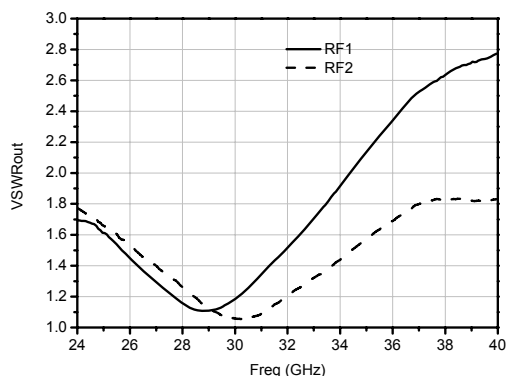
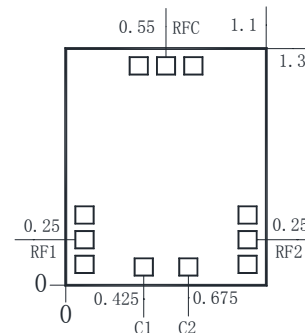
- Freq: 24~40GHz
- Insertion Loss: 3 dB
- Isolation: 33 dB
- Control Voltage: 0/-5V
- Chip Size: 1.3mm×1.1mm×0.05mm

General Description

The HG129K is a reflective GaAs pHEMT SPDT switch chip. Covering 24 to 40 GHz, this switch offers very high isolation of 33 dB and insertion loss of 3 dB. This switch operates using a negative control voltage of 0/-5V, and requires no bias supply.

Electrical Specifications ($T_A=25^\circ\text{C}$)

Parameter	Min.	Typ.	Max.
Frequency Range(GHz)	24~40		
Input VSWR	-	2	-
Output VSWR	-	1.8	-
Insertion Loss(dB)	-	3	-
Isolation(dB)	-	33	-

Input VSWR

Output VSWR

Outline Drawing (mm)

Truth Table

C1	C2	RFC to RF1	RFC to RF2
0V	-5V	OFF	ON
-5V	0V	ON	OFF

Absolute Maximum Ratings

RF Input Power	+27dBm
Operating Temperature	-55°C~125°C
Storage Temperature	-65°C~150°C

Notes:

1. The chip should be stored in a dry and nitrogen environment, and used in a clean environment.
2. GaAs material is brittle, can not touch the surface of the chip, must be careful when using.
3. The chip is welding with conductive adhesive or alloy (alloy temperature should not exceed 300°C, and no more than 30 sec.), and should make it fully grounded.
4. The chip microwave port and substrate gap is not exceeding 0.05mm, with $\Phi 25\mu\text{m}$ double gold wire bonding, suggested length of gold wire 250~400 μm .
5. Chip microwave port without DC blocking capacitor.
6. The chip is sensitive to static electricity, and should be protected against static electricity during storage and use.